



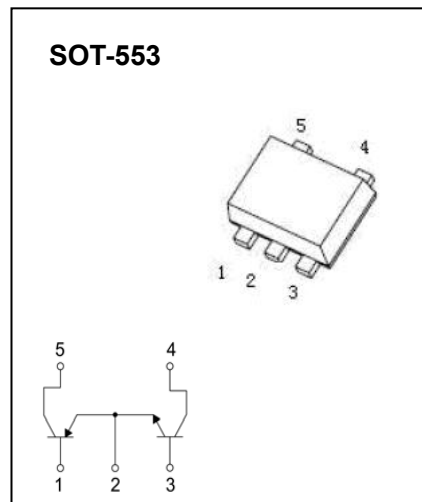
# SOT-553 Plastic-Encapsulate Transistors

**EMY1** Dual Transistors (PNP+NPN)

## FEATURES

- Includes a 2SA1037AK and a 2SC2412K transistor in a package
- PNP and NPN transistors have common emitters
- Mounting cost and area can be cut in half

Marking: Y1



Tr1 Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current	-150	mA
$P_C$	Collector Power Dissipation	150	mW
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-6\text{V}, I_C=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.50	V
Transition frequency	$f_T$	$V_{CE}=-12\text{V}, I_C=-2\text{mA}, f=100\text{MHz}$		140		MHz
Output capacitance	$C_{ob}$	$V_{CB}=-12\text{V}, I_E=0, f=1\text{MHz}$			5	pF

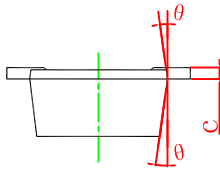
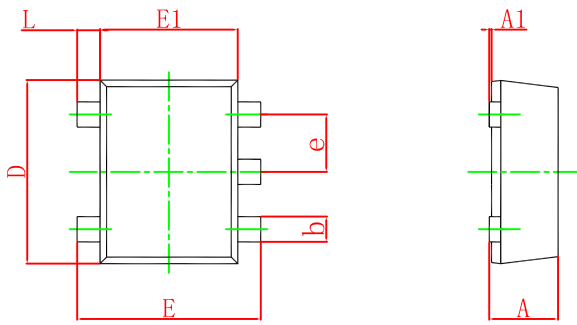
**Tr2 Absolute maximum ratings (T<sub>a</sub>=25°C)**

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current	150	mA
P <sub>C</sub>	Collector Power Dissipation	150	mW
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

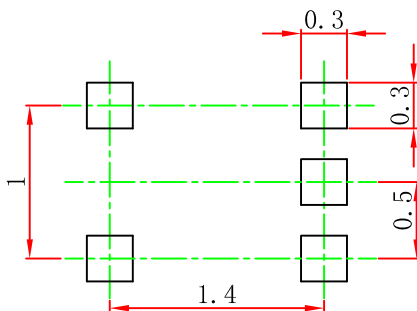
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =50μA, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =50μA, I <sub>C</sub> =0	7			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =7V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	120		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.4	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =12V, I <sub>C</sub> =2mA, f=100MHz		180		MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =12V, I <sub>E</sub> =0, f=1MHz			3.5	pF

## SOT-553 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
$\theta$	10° REF.		10° REF.	

## SOT-553 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05$  mm.
  3. The pad layout is for reference purposes only.

